

MOSFETs Silicon N-Channel MOS (π -MOSIV)

TK1P90A

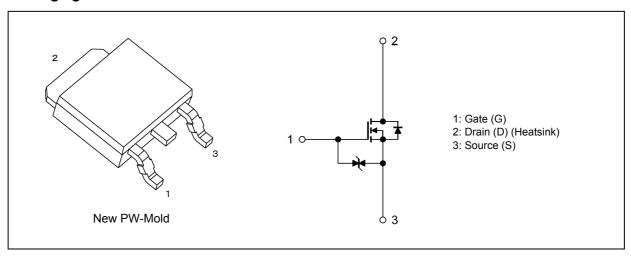
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 6.7 \Omega$ (typ.)
- (2) High forward transfer admittance: $|Y_{fs}| = 1.0 \text{ S (typ.)}$
- (3) Low leakage current: $I_{DSS} = 100 \mu A \text{ (max) (V}_{DS} = 720 \text{ V)}$
- (4) Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_{D} = 1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	900	V
Gate-source voltage		V_{GSS}	±30	
Drain current (DC)	(Note 1)	I _D	1	Α
Drain current (pulsed)	(Note 1)	I _{DP}	3	
Power dissipation (T _c = 25°C)	P_{D}	20	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	216	mJ
Avalanche current		I _{AR}	1	Α
Repetitive avalanche energy	(Note 3)	E _{AR}	2.0	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance		6.25	°C/W
Channel-to-ambient thermal resistance		125	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 396 mH, R_G = 25 Ω , I_{AR} = 1 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



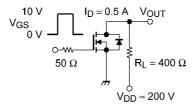
6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 720 V, V _{GS} = 0 V	_	_	100	
Gate-source breakdown voltage	V _{(BR)GSS}	$I_{G} = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$	±30			V
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	900	_		
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 0.5 A	_	6.7	9.0	Ω
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, I _D = 0.5 A	0.3	1.0		S

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	_	320	_	pF
Reverse transfer capacitance	C _{rss}		_	10	_	
Output capacitance	C _{oss}		_	35	_	
Switching time (rise time)	t _r	See Figure 6.2.1.	_	25	_	ns
Switching time (turn-on time)	t _{on}		_	60	_	
Switching time (fall time)	t _f		_	30	_	
Switching time (turn-off time)	t _{off}			155	_	



Duty \leq 1 %, $t_W^{}=$ 10 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

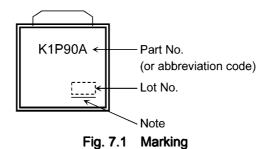
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$		13		nC
Gate-source charge	Q_{gs}		_	6	_	
Gate-drain charge	Q_{gd}		_	7	_	

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 1)	I _{DR}	_	_	_	1	Α
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	_	_	_	3	
Diode forward voltage		V_{DSF}	I _{DR} = 1 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time		t _{rr}	I _{DR} = 1 A, V _{GS} = 0 V	_	550	_	ns
Reverse recovery charge		Q _{rr}	-dI _{DR} /dt = 100 A/μs	_	2.2	_	μС



7. Marking (Note)



Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)

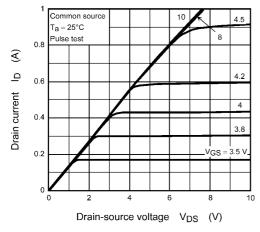


Fig. 8.1 I_D - V_{DS}

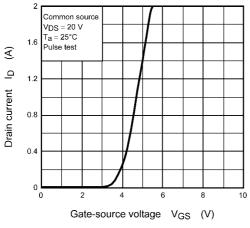


Fig. 8.3 I_D - V_{GS}

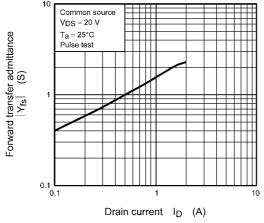


Fig. 8.5 |Y_{fs}| - I_D

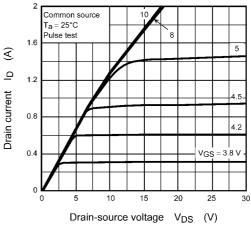


Fig. 8.2 I_D - V_{DS}

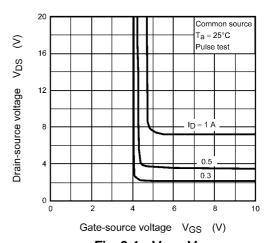


Fig. 8.4 V_{DS} - V_{GS}

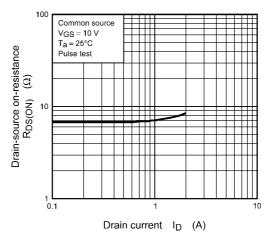


Fig. 8.6 R_{DS(ON)} - I_D

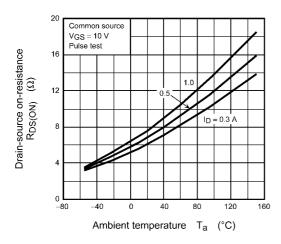


Fig. 8.7 R_{DS(ON)} - T_a

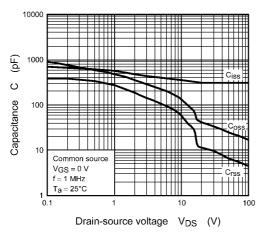


Fig. 8.9 C - V_{DS}

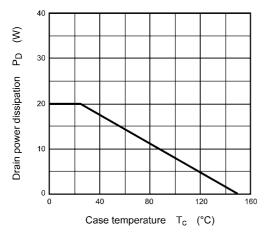


Fig. 8.11 P_D - T_c (Guaranteed Maximum)

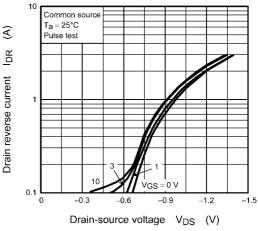


Fig. 8.8 I_{DR} - V_{DS}

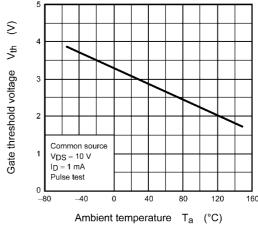


Fig. 8.10 V_{th} - T_a

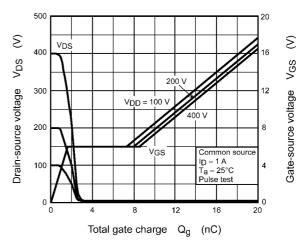


Fig. 8.12 Dynamic Input/Output Characteristics

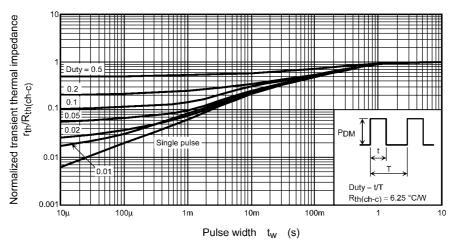


Fig. 8.13 $r_{th}/R_{th(ch-c)} - t_w$ (Guaranteed Maximum)

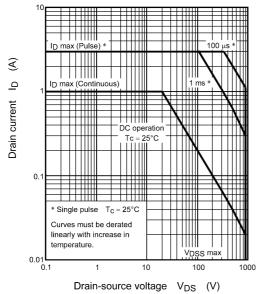


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

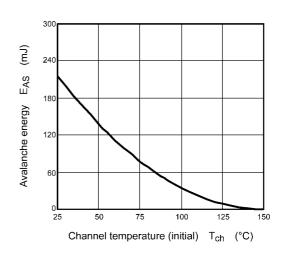


Fig. 8.15 E_{AS} - T_{ch} (Guaranteed Maximum)

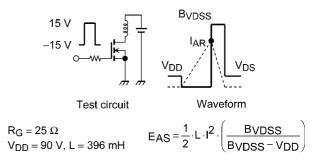


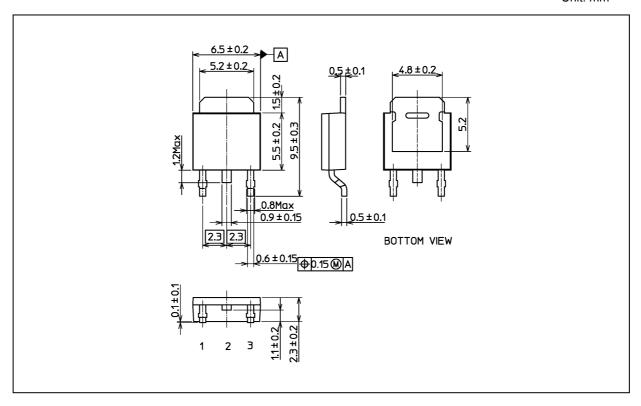
Fig. 8.16 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

Package Name(s)	
TOSHIBA: 2-7J1S	
Nickname: New PW-Mold	



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